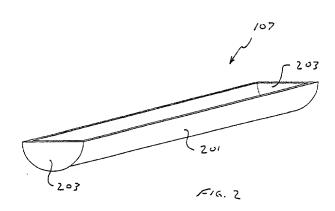
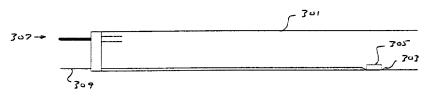
In re application of Yuri V. Melnik, et al.
Express Mail No. EL828015510US
Atty. David G. Beck (415) 393-2404
Atty. Docket No. 2366-7005
Page 1 of 3

F16. 1





F16. 3

Atty. Docket No. 2366-7005 Page 2 of 3 INTRODUCE HALIDE GAS GaN GROWN ON FLUSH/FILL REACTOR INTO Ga SOURCE TUBE WITH INERT GAS SUBSTRATES LOWER GROWTH ZONE TRANSPORT GALLIUM TEMPERATURE TO CHLORIDE TO GROWTH HEAT SUBSTRATES -403 ACHIEVE RAPID ZONE CRYSTAL GROWTH STOP HCI AND AMMONIA DELIVER AMMONIA GAS 413 MELT Ga SOURCE GAS FLOW AND COOL TO GROWTH ZONE CRYSTALS 421 HEAT Ga SOURCE AMMONIA GAS AND 407 (2 TEMPERATURE GALLIUM CHLORIDE F16.4 RANGES) REACT INTRODUCE HALIDE GAS LOWER GROWTH ZONE FLUSH/FILL REACTOR INTO Ga SOURCE TUBE TEMPERATURE TO WITH INERT GAS & SELECTED AI SOURCE ACHIEVE RAPID TUBE CRYSTAL GROWTH 419 GALLIUM CHLORIDE AND 605 HEAT SECOND AI **HEAT SUBSTRATES** ALUMINUM TRICHLORIDE SOURCE FORMED 613 GALLIUM CHLORIDE AND INTRODUCE HALIDE GAS ALUMINUM TRICHLORIDE -405 INTO SECOND AI MELT Ga SOURCE TRANSPORTED TO SOURCE TUBE **GROWTH ZONE** 615 TRANSPORT ALUMINUM HEAT Ga SOURCE 609 DELIVER AMMONIA GAS TRICHLORIDE FROM (2 TEMPERATURE 407 TO GROWTH ZONE SECOND ALSOURCE TO RANGES) GROWTH ZONE GAS FLOW TO FIRST AI AlGaN GROWN ON HEAT ONE AI SOURCE SOURCE STOPPED AND SUBSTRATES SOURCE WITHDRAWN 619 STOP HCI AND AMMONIA GAS FLOW AND COOL CRYSTALS 421

F16. 6

In re application of Yuri V. Melnik, et al. Express Mail No. EL828015510US Atty. David G. Beck (415) 393-2404

